Description

The VST20N100 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

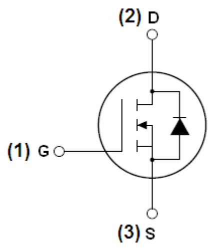
General Features

- V_{DS} =200V,I_D =100A
  $R_{DS(ON)}$ <11mΩ @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

TO-263



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST20N100-T3	VST20N100	TO-263	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	100	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	70.7	A
Pulsed Drain Current	I_{DM}	400	A
Maximum Power Dissipation	P_D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	1216	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case(Note 2)	$R_{\theta JC}$	0.5	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

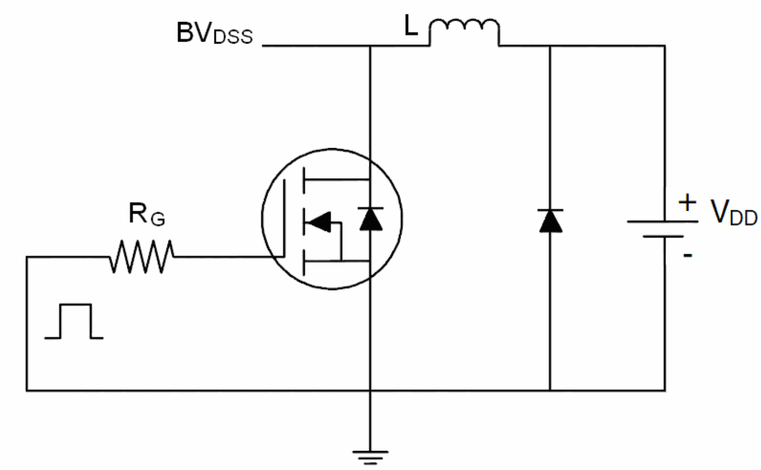
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	200	230	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=200V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.5		4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=50A	-	10	11	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=50A	70	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=100V,V_{GS}=0V, F=1.0MHz	-	4200	5500	PF
Output Capacitance	C_{oss}		-	333.1	450	PF
Reverse Transfer Capacitance	C_{rss}		-	8.8	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=100V,I_D=50A V_{GS}=10V,R_G=4.7Ω	-	18	-	nS
Turn-on Rise Time	t_r		-	26	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	41	-	nS
Turn-Off Fall Time	t_f		-	11	-	nS
Total Gate Charge	Q_g	V_{DS}=100V,I_D=50A, V_{GS}=10V	-	63.2		nC
Gate-Source Charge	Q_{gs}		-	24		nC
Gate-Drain Charge	Q_{gd}		-	16.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=100A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	100	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = 50 di/dt = 100A/μs(Note3)	-	140		nS
Reverse Recovery Charge	Qrr		-	600		nC

Notes:

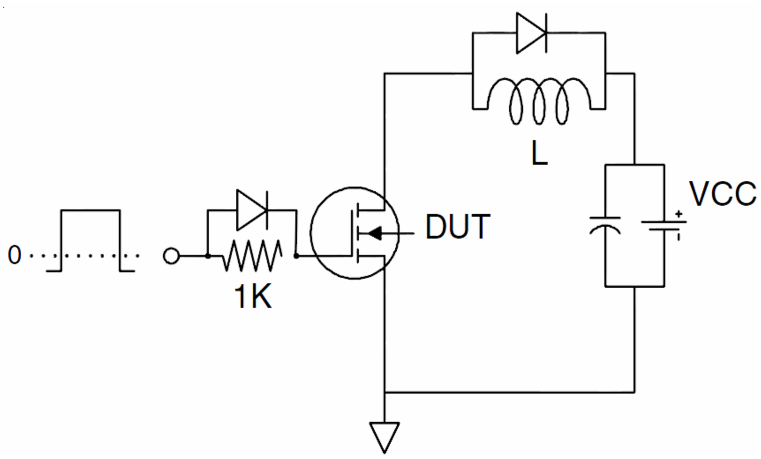
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : Tj=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω

Test Circuit

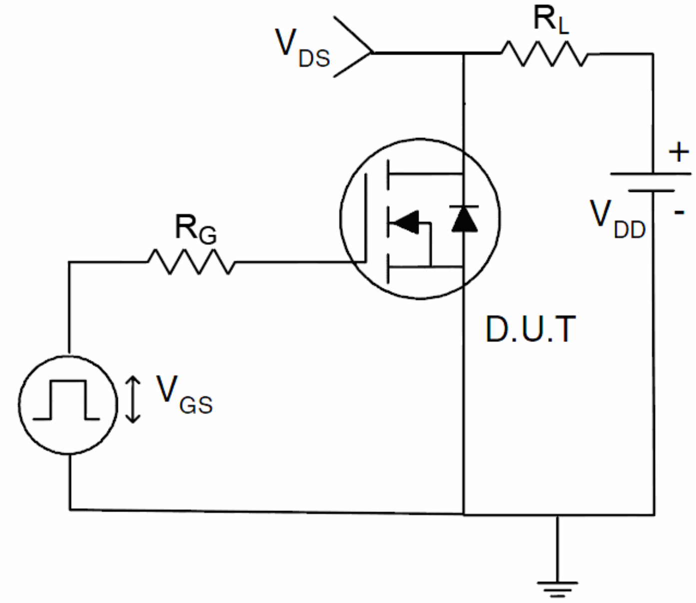
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

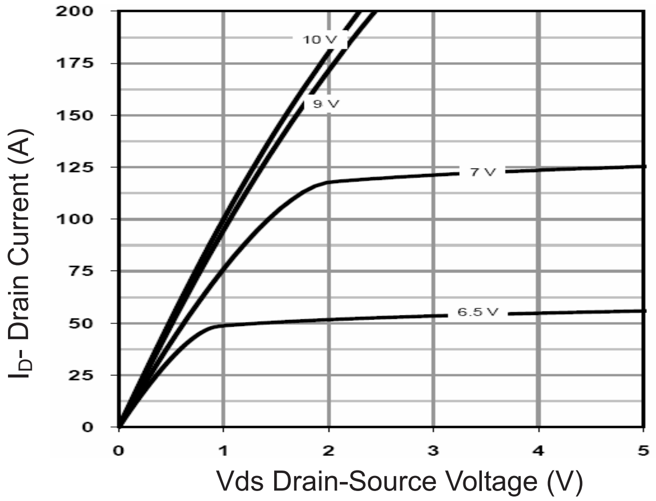


Figure 1 Output Characteristics

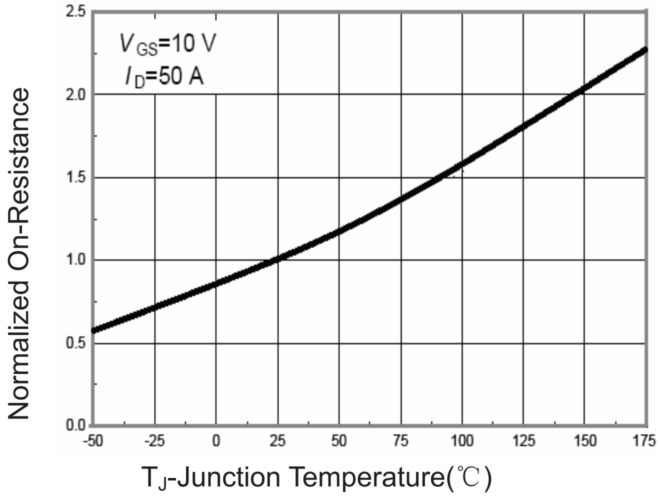


Figure 4 Rdson-JunctionTemperature

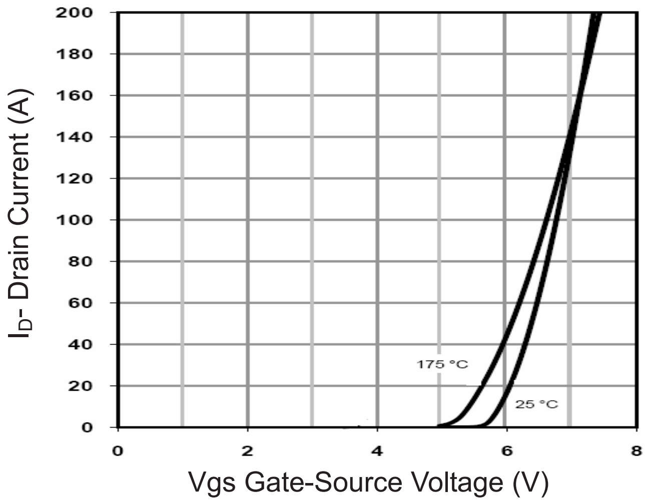


Figure 2 Transfer Characteristics

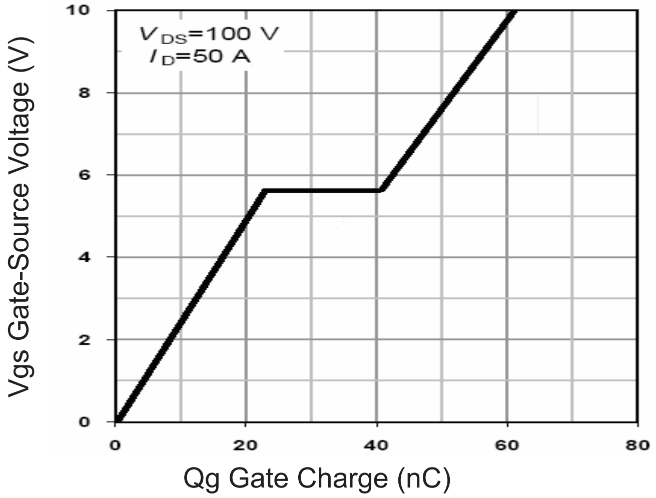


Figure 5 Gate Charge

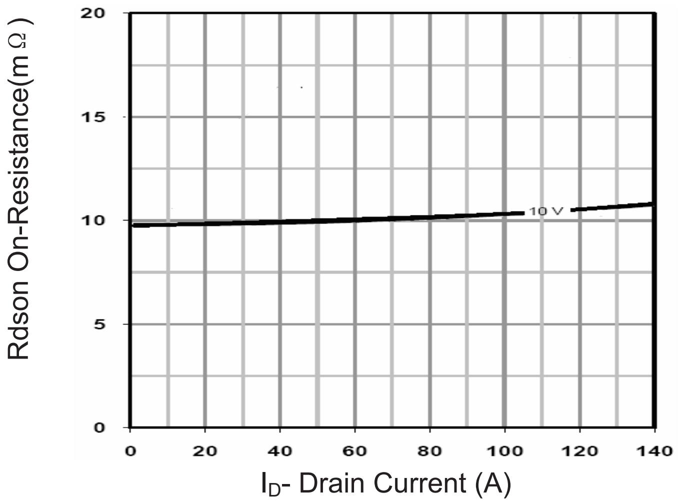


Figure 3 Rdson- Drain Current

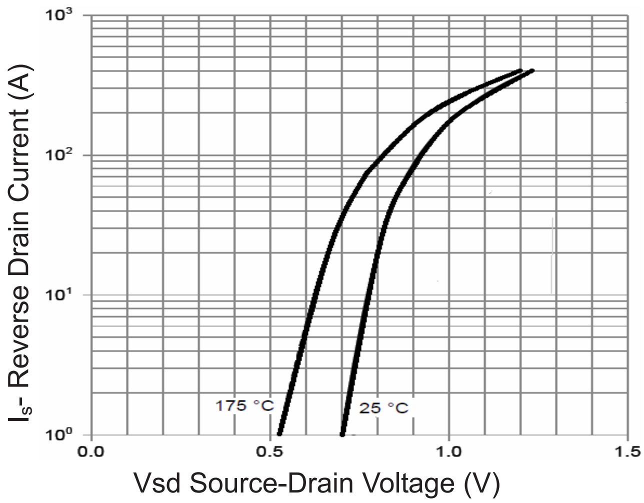


Figure 6 Source- Drain Diode Forward

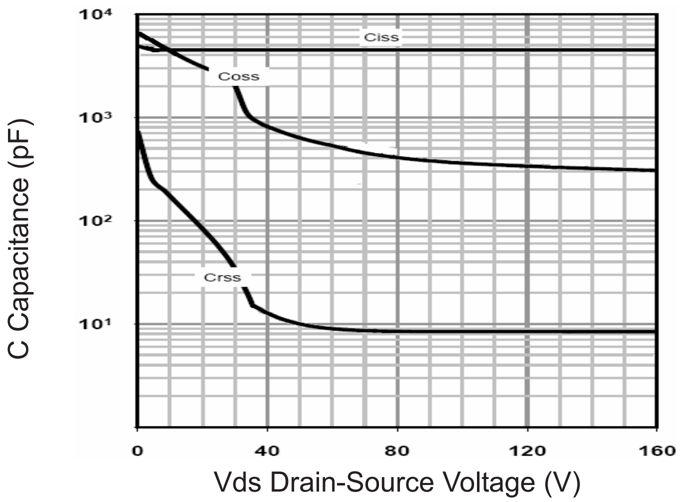


Figure 7 Capacitance vs Vds

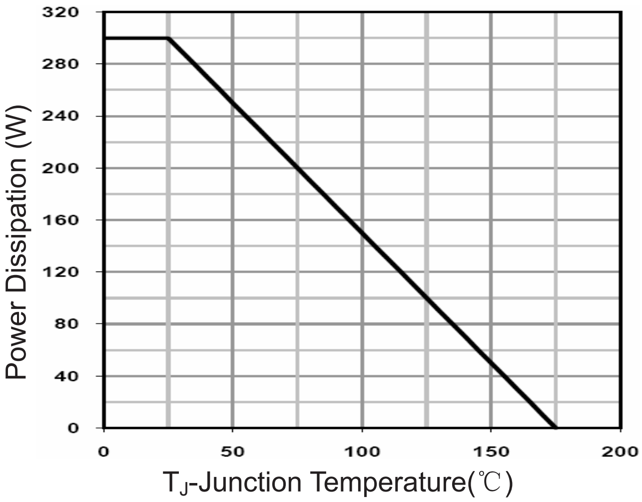


Figure 9 Power De-rating

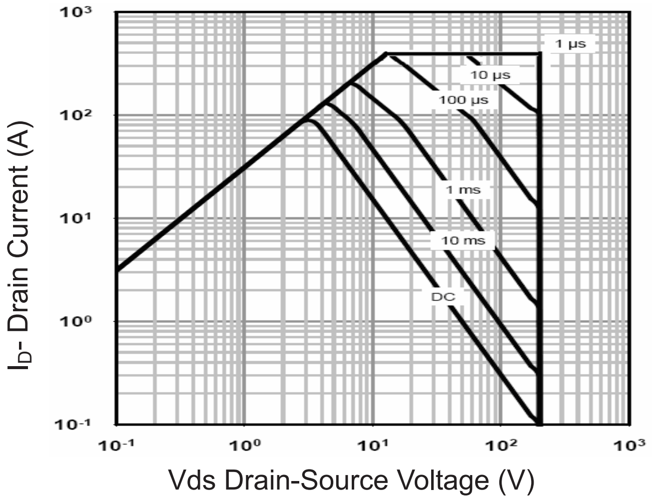


Figure 8 Safe Operation Area

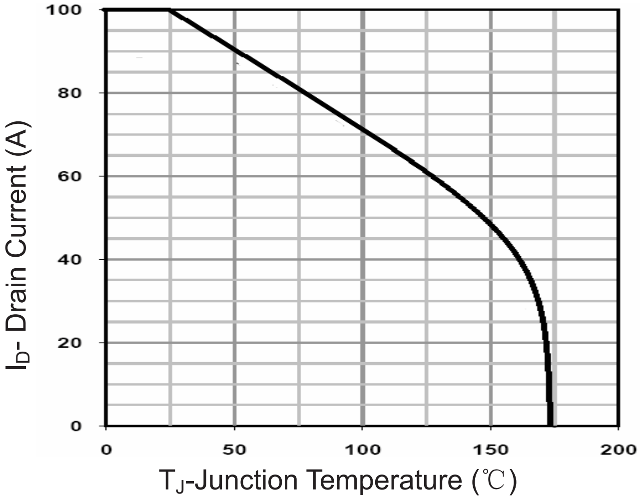


Figure 10 Current De-rating

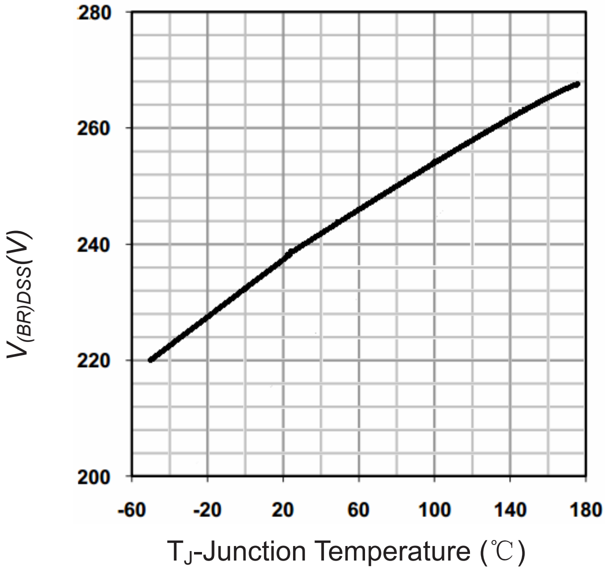


Figure 11 Drain-source breakdown voltage

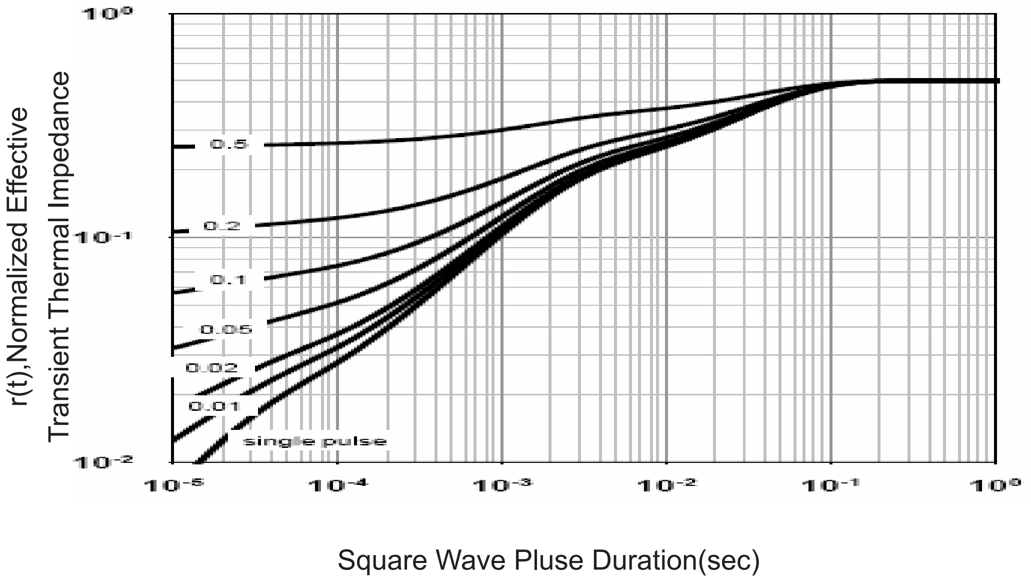


Figure 12 Normalized Maximum Transient Thermal Impedance